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# May 2009

# **FDMS8670**

# N-Channel Power Trench® MOSFET 30V, 42A, 2.6m $\Omega$

#### **Features**

- Max  $r_{DS(on)}$  = 2.6m $\Omega$  at  $V_{GS}$  = 10V,  $I_D$  = 24A
- Max  $r_{DS(on)}$  = 3.8m $\Omega$  at  $V_{GS}$  = 4.5V,  $I_D$  = 18A
- 100% UIL Tested
- RoHS Compliant

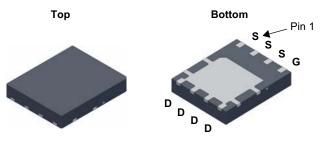


#### **General Description**

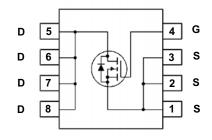
This N-Channel MOSFET is produced using Fairchild Semiconductor's latest proprietary Power Trench® process that has been especially tailored to minimize on-resistance. This part exhibits industry leading switching FOM (RDS\*Qgd) to enhance DC-DC synchronous rectifier efficiency.

# **Application**

■ DC - DC Conversion







# MOSFET Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V <sub>DS</sub>	Drain to Source Voltage			30	V
$V_{GS}$	Gate to Source Voltage			±20	V
	Drain Current -Continuous (Package limited)	T <sub>C</sub> = 25°C		42	
I <sub>D</sub>	-Continuous (Silicon limited)	T <sub>C</sub> = 25°C		135	
	-Continuous	T <sub>A</sub> = 25°C	(Note 1a)	24	A
	-Pulsed			150	
E <sub>AS</sub>	Single Pulse Avalanche Energy		(Note 3)	288	mJ
Б	Power Dissipation	T <sub>C</sub> = 25°C		78	w
$ P_{D} $	Power Dissipation	T <sub>A</sub> = 25°C	(Note 1a)	2.5	— vv
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature R	ange		-55 to +150	°C

#### **Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.6	°C/W
R <sub>e.IA</sub>	Thermal Resistance, Junction to Ambient	(Note 1a)	50	C/VV

# **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS8670	FDMS8670	Power 56 13"		12 mm	3000 units

# **Electrical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, referenced to 25°C		19.5		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 24V,			1	μА
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA

#### On Characteristics

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.0	1.7	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, referenced to 25°C		-5.9		mV/°C
		V <sub>GS</sub> = 10V, I <sub>D</sub> = 24A		2.1	2.6	
r <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 18A		3.0	3.8	mΩ
		V <sub>GS</sub> = 10V, I <sub>D</sub> = 24A, T <sub>J</sub> = 125°C		3.0	3.8	
9 <sub>FS</sub>	Forward Transconductance	$V_{DD} = 5V, I_{D} = 24A$		117		S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V - 45V V - 0V		2965	3940	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1MHz		1395	1855	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			180	265	pF
$R_g$	Gate Resistance	f = 1MHz		1.3		Ω

# **Switching Characteristics**

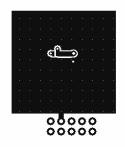
t <sub>d(on)</sub>	Turn-On Delay Time		$V_{DD}$ = 15V, $I_{D}$ = 24A, $V_{GS}$ = 10V, $R_{GEN}$ = 6 $\Omega$		14	24	ns
t <sub>r</sub>	Rise Time				5	10	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>GS</sub> = 10V, R <sub>GEN</sub>			33	53	ns
t <sub>f</sub>	Fall Time				4	10	ns
$Q_g$	Total Gate Charge	V <sub>GS</sub> = 0V to 10V			45	63	nC
Qg	Total Gate Charge	V <sub>GS</sub> = 0V to 5V	V <sub>DD</sub> = 15V,		23	33	nC
Q <sub>gs</sub>	Gate to Source Charge		I <sub>D</sub> = 24A		8.3		nC
$Q_{gd}$	Gate to Drain "Miller" Charge				5.7		nC

## **Drain-Source Diode Characteristics**

V Source to Drain Diade, Ferward Voltage	$V_{GS} = 0V, I_S = 24A$ (Note 2)		0.8	1.3	\/	
V <sub>SD</sub>	Source to Drain Diode Forward Voltage	$V_{GS} = 0V, I_S = 2.1A$ (Note 2)		0.7	1.2	<b>'</b>
t <sub>rr</sub>	Reverse Recovery Time			44	71	ns
Q <sub>rr</sub>	Reverse Recovery Charge			27	43	nC

#### NOTES

<sup>1.</sup> R<sub>0,1A</sub> is determined with the device mounted on a 1in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>0,1C</sub> is guaranteed by design while R<sub>0,CA</sub> is determined by the user's board design.



a.  $50^{\circ}$ C/W when mounted on a  $1 \text{ in}^2$  pad of 2 oz copper.



b. 125°C/W when mounted on a minimum pad of 2 oz copper.

- 2. Pulse Test: Pulse Width < 300 $\mu$ s, Duty cycle < 2.0%.
- 3. Starting  $T_J$  = 25°C, L = 1mH,  $I_{AS}$  = 24A,  $V_{DD}$  = 27V,  $V_{GS}$  = 10V.

# Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

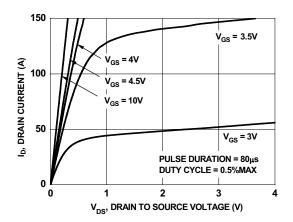


Figure 1. On-Region Characteristics

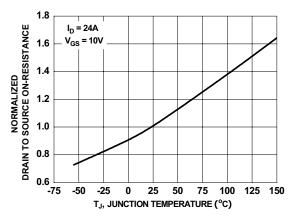


Figure 3. Normalized On-Resistance vs Junction Temperature

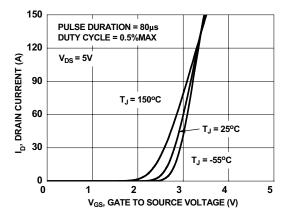


Figure 5. Transfer Characteristics

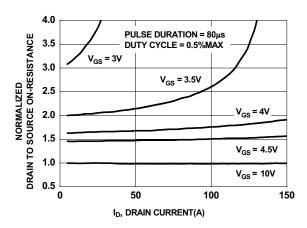


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

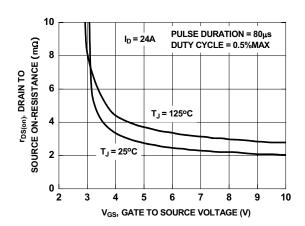


Figure 4. On-Resistance vs Gate to Source Voltage

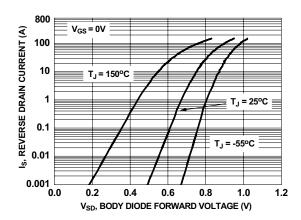


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

# Typical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

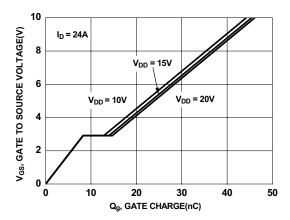


Figure 7. Gate Charge Characteristics

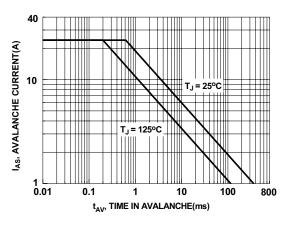


Figure 9. Unclamped Inductive Switching Capability

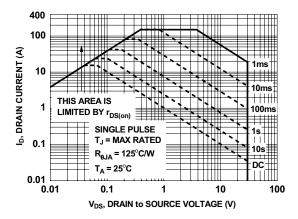


Figure 11. Forward Bias Safe Operating Area

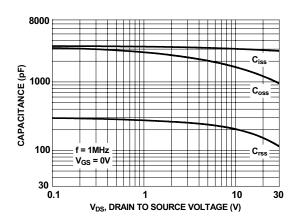


Figure 8. Capacitance vs Drain to Source Voltage

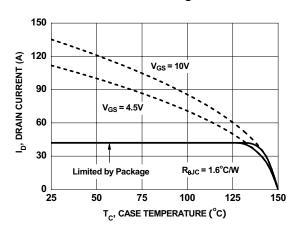


Figure 10. Maximum Continuous Drain Current vs Case Temperature

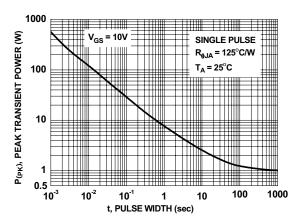


Figure 12. Single Pulse Maximum Power Dissipation

# Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

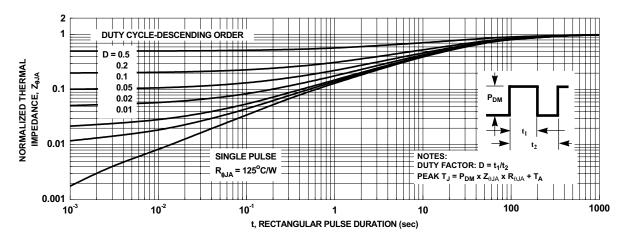


Figure 13. Transient Thermal Response Curve

#### **Dimensional Outline and Pad Layout** 5.00 A 1.27 PKG 8 5 0.77 4.52 PKG & 6.00 6.61 1.27 PIN #1 IDENT MÄY TOP VIEW APPEAR AS OPTIONAL 0.61 1.27 SEE DETAIL A LAND PATTERN RECOMMENDATION SIDE VIEW OPTIONAL DRAFT ANGLE MAY APPEAR 5.00 ON FOUR SIDES 3.81 OF THE PACKAGE 1.27 0.46 0.36 (8X) (0.39)⊕ 0.10M C A B 0.71 6.15 5.75 $4.01 \pm 0.30$ CHAMFER CORNER AS PIN #1 0.71 IDENT MÄY APPEAR AS OPTIONAL OPTIONAL TIE BARS MAY 5 6 APPEAR ON THESE AREAS (MAX. TIE BAR PROTRUSION: 0.15mm) BOTTOM VIEW NOTES: UNLESS OTHERWISE SPECIFIED PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA, DATED OCTOBER 2002. // 0.10 C DATED OCTOBER 2002. ALL DIMENSIONS ARE IN MILLIMETERS. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH, MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994. ○ 0.08 C DRAWING FILE NAME: PQFN08AREV4 Ċ 0.05 1.10 0.90 SEATING PLANE DETAIL A Α





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